2SD2479

Silicon NPN epitaxial planar type

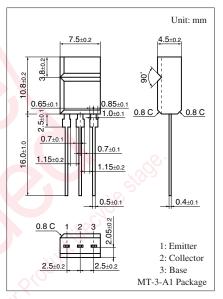
For low-frequency amplification

Features

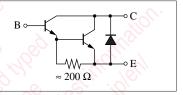
- \bullet High forward current transfer ratio h_{FE}
- Allowing supply with the radial taping

Absolute Maximum Hatings $T_a = 25$ C							
Parameter	Symbol	Rating	Unit				
Collector-base voltage (Emitter open)	V _{CBO}	120	v				
Collector-emitter voltage (Base open)	V _{CEO}	100	v				
Emitter-base voltage (Collector open)	V _{EBO}	5	V				
Collector current	I _C	2	А				
Peak collector current	I _{CP}	3	А				
Collector power dissipation	P _C	1.5	W				
Junction temperature	Tj	150	°C				
Storage temperature	T _{stg}	-55 to +150	°C				
			1				





Internal Connection



Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = 100 \ \mu \text{A}, I_{\rm E} = 0$	120	SO.		V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = 1 \text{ mA}, I_{\rm B} = 0$	100			V
Emitter-base voltage (Collector open)	V _{EBO}	$I_{\rm E} = 100 \ \mu A, I_{\rm C} = 0$.5			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = 25 \text{ V}, I_E = 0$			0.1	μΑ
Emitter-base cutoff current (Collector open)	I _{EBO}	$V_{EB} = 4 V, I_C = 0$			1	μΑ
Forward current transfer ratio *1, 2	h _{FE}	$V_{CE} = 10 \text{ V}, I_C = 1 \text{ A}$	4 0 0 0		40 000	
Collector-emitter saturation voltage *1	V _{CE(sat)}	$I_{\rm C} = 1 {\rm A}, I_{\rm B} = 1 {\rm mA}$			1.5	V
Base-emitter saturation voltage *1	V _{BE(sat)}	$I_{\rm C} = 1 {\rm A}, I_{\rm B} = 1 {\rm mA}$			2	V
Transition frequency	f _T	$V_{CB} = 10 \text{ V}, I_E = -50 \text{ mA}, f = 200 \text{ MHz}$		150		MHz

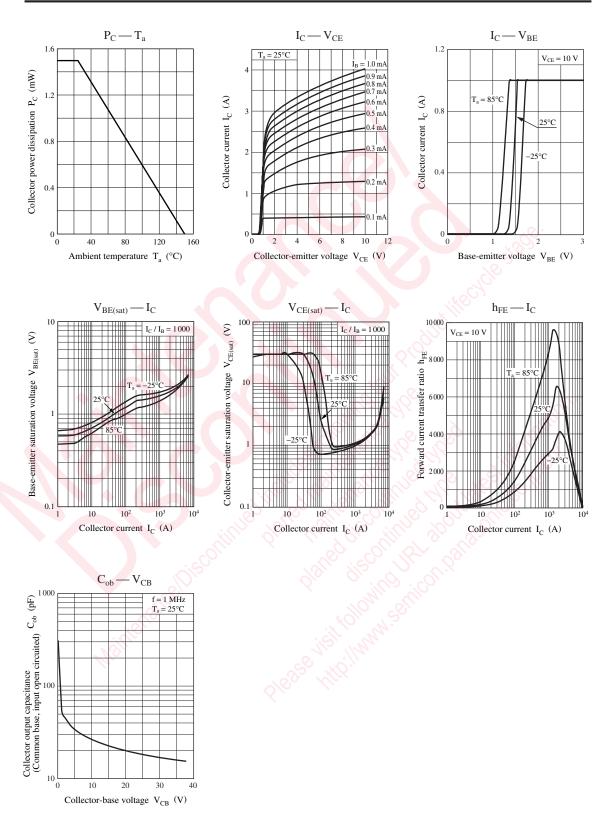
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *1: Pulse measurement

*2: Rank classification

Rank	Q	R	S
h _{FE}	4000 to 10000	8000 to 20000	16000 to 40000

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